

Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/716,249 on August 12, 2005

Combined classifications

12 257/E21.651  
10 257/301  
10 257/E27.092  
8 257/E27.094  
7 257/296  
7 257/305  
5 257/304  
5 257/E21.648  
5 438/392  
4 257/303  
4 257/311  
4 257/E21.008  
4 257/E27.089  
4 438/243  
4 438/244  
4 438/249  
3 257/306  
3 257/465  
3 257/466  
3 257/E21.646  
3 257/E27.096  
3 365/149  
3 438/242  
3 438/386  
2 257/300  
2 257/307  
2 257/382  
2 257/448  
2 257/461  
2 257/462  
2 257/618  
2 257/E21.143  
2 257/E21.151  
2 257/E21.396  
2 257/E21.538  
2 257/E21.645  
2 257/E21.65  
2 257/E21.652  
2 257/E21.653  
2 257/E27.086  
2 257/E27.093  
2 257/E27.095  
2 257/E27.112  
2 257/E27.131  
2 257/E27.133  
2 257/E29.262  
2 257/E29.267  
2 365/182  
2 438/152  
2 438/239  
2 438/254  
2 438/259  
2 438/270  
2 438/302  
2 438/387  
2 438/388  
2 438/389  
2 438/73  
2 438/977

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Titles of Most Frequently Occurring Classifications of Patents Returned  
From A Search of 10/716,249 on August 12, 2005

10 257/301 (6 OR, 4 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of 10 15 cm <sup>-3</sup> or less)  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/296 ..Insulated gate capacitor or insulated gate  
transistor combined with capacitor (e.g., dynamic memory  
cell)  
257/301 ...Capacitor in trench

7 257/296 (3 OR, 4 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of 10 15 cm <sup>-3</sup> or less)  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/296 ..Insulated gate capacitor or insulated gate  
transistor combined with capacitor (e.g., dynamic memory  
cell)  
7 257/305 (2 OR, 5 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of 10 15 cm <sup>-3</sup> or less)  
257/288 .Having insulated electrode (e.g., MOSFET, MOS  
diode)  
257/296 ..Insulated gate capacitor or insulated gate  
transistor combined with capacitor (e.g., dynamic  
memory cell)  
257/301 ...Capacitor in trench  
257/305 ....with means to insulate adjacent storage  
nodes (e.g., channel stops or field oxide)

5 257/304 (2 OR, 3 XR)  
Class 257 : ACTIVE SOLID-STATE DEVICES  
257/264 ...Enhancement mode or with high resistivity  
channel (e.g., doping of 10 15 cm <sup>-3</sup> or less)  
257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)  
257/296 ..Insulated gate capacitor or insulated gate  
transistor combined with capacitor (e.g., dynamic  
memory cell)  
257/301 ...Capacitor in trench  
257/304 ....Storage node isolated by dielectric from  
semiconductor substrate

5 438/392 (1 OR, 4 XR)  
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS  
438/381 MAKING PASSIVE DEVICE (E.G., RESISTOR, CAPACITOR, ETC.)  
438/386 .Trench capacitor  
438/389 ..Including doping of trench surfaces  
438/392 ...Doping by outdiffusion from a dopant source layer (e.g.,  
doped oxide)

PLUS Search Results for S/N 10/716,249, Searched August 12, 2005

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA.

5371032	5521111	5187550	6107153	5466636
5414285	4988637	5217918	6121651	5498564
5330936	5223730	5234854	4797373	5543348
6232626	5234856	5262662	4833094	5563433
6500692	6249017	5321285	4958206	5627092
6611037	5026659	5702969	5185292	5670805
6730980	5386131	5732014	5225697	5824582
6767759	4954854	5753549	5309008	5885863
6838742	4967248	5897351	5411905	5892707
5198995	5021355	5900659	5448090	5937296